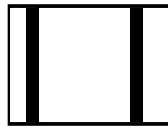


AQ1026 Series 15pF 30kV Bidirectional Discrete TVS



Pinout



Functional Block Diagram



Description

The AQ1026 back-to-back diodes are fabricated in a proprietary silicon avalanche technology. These diodes provide a high ESD (electrostatic discharge) protection level for electronic equipment. The AQ1026 TVS can safely absorb repetitive ESD strikes at $\pm 30\text{kV}$ (contact discharge, IEC 61000-4-2) without performance degradation. Additionally, each diode can safely dissipate 5A of 8/20 μs surge current (IEC 61000-4-5 2nd edition) with very low clamping voltages.

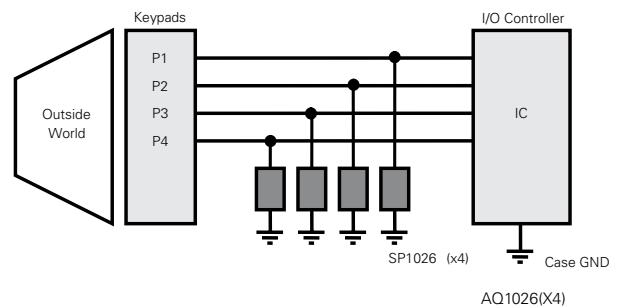
Features

- ESD, IEC 61000-4-2, $\pm 30\text{kV}$ contact, $\pm 30\text{kV}$ air
- EFT, IEC 61000-4-4, 40A (5/50ns)
- Lightning, IEC 61000-4-5 2nd edition, 5A (8/20 μs)
- Low leakage current of 0.5 μA (MAX) at 5V
- ESD, ISO 10605, 330pF 330 Ω , $\pm 25\text{kV}$ contact, $\pm 30\text{kV}$ air
- Space efficient 0201 footprint)
- AEC-Q101 qualified
- Halogen free, lead free and RoHS compliant
- Moisture Sensitivity Level (MSL -1)
- PPAP Capable

Applications

- Mobile phones
- Smart phones
- Smart watches
- Tablets
- Portable navigation components
- Portable medical components
- Automotive applications

Application Example



Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
I_{PP}	Peak Pulse Current ($t_p=8/20\mu s$)	5	A
T_{OP}	Operating Temperature	-40 to 150	°C
T_{STOR}	Storage Temperature	-55 to 150	°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the component. This is a stress only rating and operation of the component at these or any other conditions above those indicated in the operational sections of this specification is not implied.

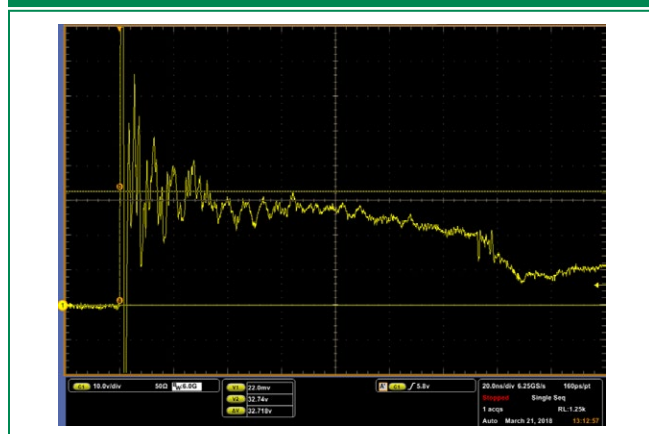
Electrical Characteristics ($T_{OP}=25^{\circ}C$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V_{RWM}	$I_R=1\mu A$			6.0	V
Breakdown Voltage	V_{BR}	$I_R=1mA$		7.8		V
Reverse Leakage Current	I_{LEAK}	$V_R=5V$		0.1	0.5	μA
Clamp Voltage ¹	V_C	$I_{PP}=1A, t_p=8/20\mu s$		12.0		V
		$I_{PP}=2A, t_p=8/20\mu s$		13.4		V
Dynamic Resistance ²	R_{DYN}	$(V_{C2} - V_{C1}) / (I_{PP2} - I_{PP1})$		0.4		Ω
ESD Withstand Voltage ¹	V_{ESD}	IEC 61000-4-2 (Contact Discharge)	± 30			kV
		IEC 61000-4-2 (Air Discharge)	± 30			kV
Diode Capacitance ¹	$C_{I/O-I/O}$	Reverse Bias=0V, f=1MHz		15		pF
		Reverse Bias=2.5V, f=1MHz		12		pF

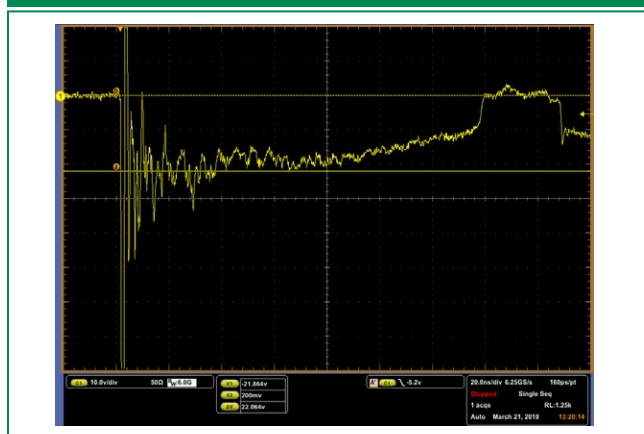
Note: ¹ Parameter is guaranteed by design and/or component characterization

² Transmission Line Pulse (TLP) with 100ns width, 2ns rise time, and average window $t_1=70ns$ to $t_2=90ns$

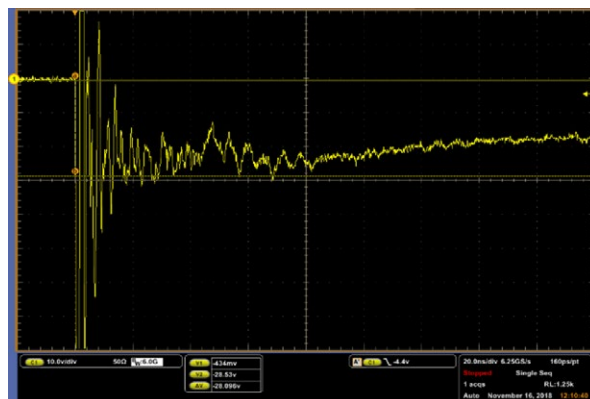
IEC 61000-4-2 +8 kV Contact ESD Clamping Voltage



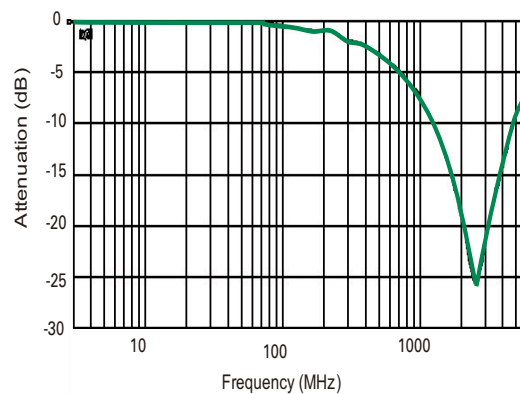
IEC 61000-4-2 -8 kV Contact ESD Clamping Voltage



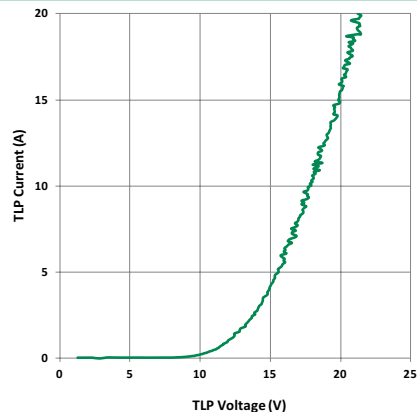
ESD ISO10605 -8 kV Contact ESD Clamping Voltage



Insertion Loss (S21) I/O to GND

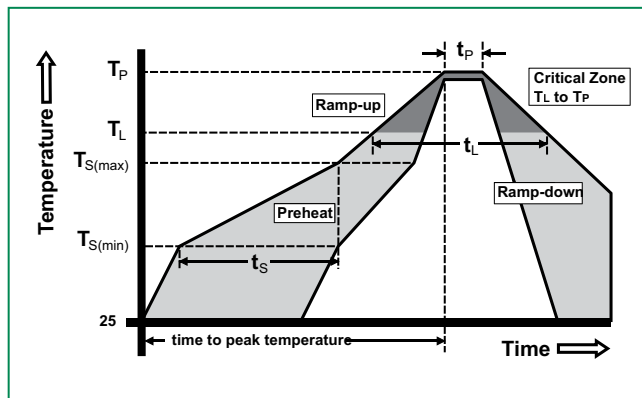


Transmission Line Pulsing(TLP) Plot



Soldering Parameters

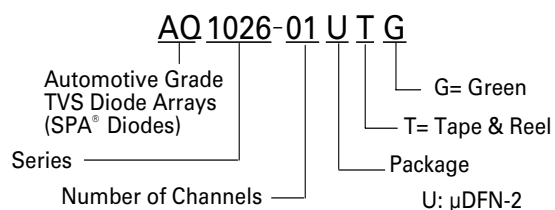
Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus) Temp (T_L) to peak		3°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_P)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		6°C/second max
Time 25°C to peak Temperature (T_P)		8 minutes Max.



Product Characteristics

Lead Plating	Pre-Plated Frame
Lead Material	Copper Alloy
Substrate material	Silicon
Body Material	Molded Compound
Flammability	UL Recognized compound meeting flammability rating V-0

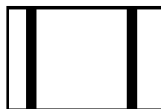
Part Numbering System



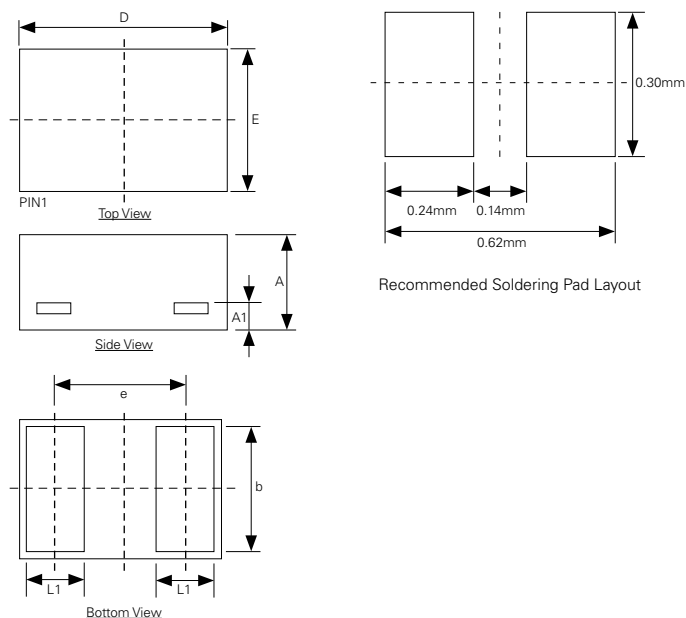
Ordering Information

Part Number	Package	Min. Order Qty.
AQ1026-01UTG	μDFN-2	15000

Part Marking System

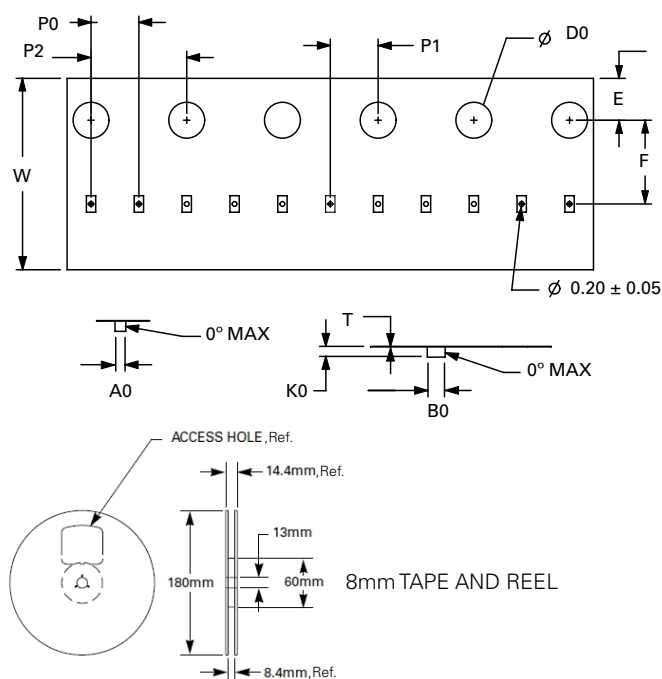


Package Dimensions — μ DFN-2 (0201)



Symbol	DIMENSIONS (mm)		
	Min.	Nor.	Max.
A	0.30	0.31	0.32
A1	0.00	0.02	0.05
b	0.18	0.23	0.28
L1	0.12	0.17	0.22
L2	0.13	0.18	0.23
D	0.55	0.60	0.65
E	0.25	0.30	0.35
e	0.35 BSC		

Embossed Carrier Tape & Reel Specification — μ DFN-2



Symbol	Millimetres		Inches	
	Min	Max	Min	Max
A0	0.33	0.40	0.013	0.016
B0	0.63	0.70	0.025	0.028
D0	1.40	1.60	0.055	0.063
E	1.65	1.85	0.065	0.073
F	3.45	3.55	0.136	0.140
K0	0.30	0.39	0.012	0.015
P0	1.90	2.10	0.075	0.083
P1	1.95	2.05	0.077	0.081
P2	3.90	4.10	0.154	0.161
T	0.13	0.25	0.005	0.010
W	7.90	8.30	0.311	0.327

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